ALPHA & OMEGA SEMICONDUCTOR

AON7536

30V N-Channel AlphaMOS

General Description

- Latest Trench Power AlphaMOS (αMOS LV) technology
- Very Low $R_{DS(ON)}$ at 4.5V V_{GS}
- Low Gate Charge
- High Current Capability
- RoHS and Halogen-Free Compliant

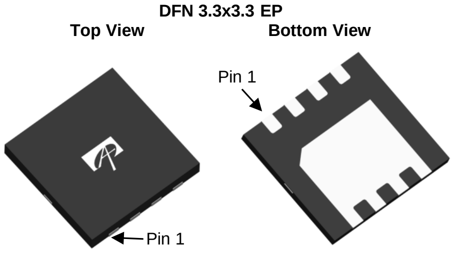
Product Summary

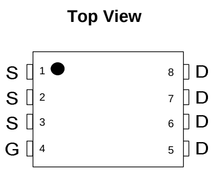
V_{DS}	30V
I_D (at V_{GS}=10V)	68A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 4.2mΩ
$R_{DS(ON)}$ (at V_{GS}=4.5V)	< 6.2mΩ

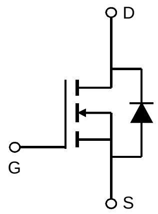
Application

- DC/DC Converters in Computing, Servers, and POL
- Isolated DC/DC Converters in Telecom and Industrial

100% UIS Tested
100% R_g Tested







Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25℃	I_D	68	A
	T_C=100℃		43	
Pulsed Drain Current [C]		I_{DM}	150	
Continuous Drain Current	T_A=25℃	I_{DSM}	24	A
	T_A=70℃		19	
Avalanche Current [C]		I_{AS}	60	A
Avalanche energy L=0.01mH [C]		E_{AS}	18	mJ
V_{DS} Spike	100ns	V_{SPIKE}	36	V
Power Dissipation [B]	T_C=25℃	P_D	32.5	W
	T_C=100℃		13	
Power Dissipation [A]	T_A=25℃	P_{DSM}	4.1	W
	T_A=70℃		2.6	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	℃

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	25	30	℃/W
Maximum Junction-to-Ambient [A D]	Steady-State		50	60	℃/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	3.1	3.8	℃/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	ID=250µA, V_{GS}=0V		30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V				1	µA
			T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±20V				±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=$V_{GS,}$ I_D=250µA		1.4	1.8	2.2	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A			3.5	4.2	mΩ
			T_J=125°C		5.3	6.4	
		V_{GS}=4.5V, I_D=20A			4.9	6.2	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A			72		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V			0.68	1	V
I_S	Maximum Body-Diode Continuous Current					36	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz			1950	2350	pF
C_{oss}	Output Capacitance				480	630	pF
C_{rss}	Reverse Transfer Capacitance				80	140	pF
R_g	Gate resistance	f=1MHz		0.2	0.5	1.0	Ω
SWITCHING PARAMETERS							
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=20A			28	40	nC
Q_g(4.5V)	Total Gate Charge				12.7	20	nC
Q_{gs}	Gate Source Charge				5.6	12	nC
Q_{gd}	Gate Drain Charge				4.4	10	nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=0.75Ω, R_{GEN}=3Ω			7.5	16	ns
t_r	Turn-On Rise Time				3	8	ns
$t_{D(off)}$	Turn-Off DelayTime				21	30	ns
t_f	Turn-Off Fall Time				2	7	ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, dI/dt=500A/µs			14.2		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, dI/dt=500A/µs			31		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on R $_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Single pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C. The SOA curve provides a single pulse rating.
G. The maximum current rating is package limited.
H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

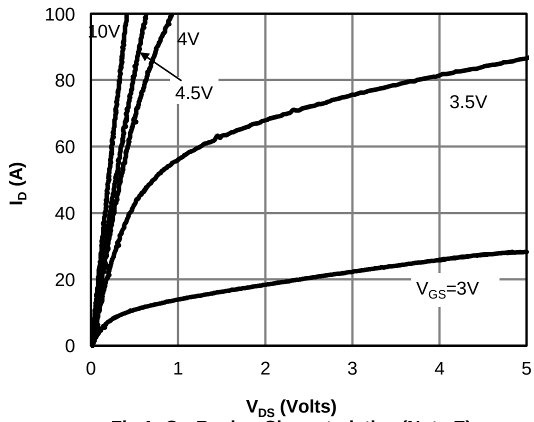


Fig 1: On-Region Characteristics (Note E)

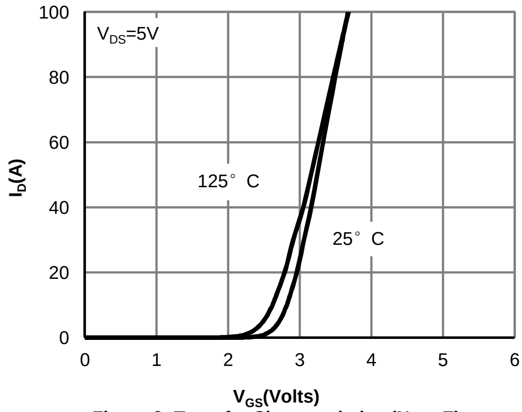


Figure 2: Transfer Characteristics (Note E)

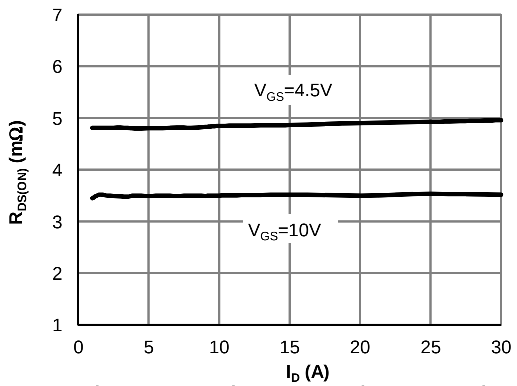


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

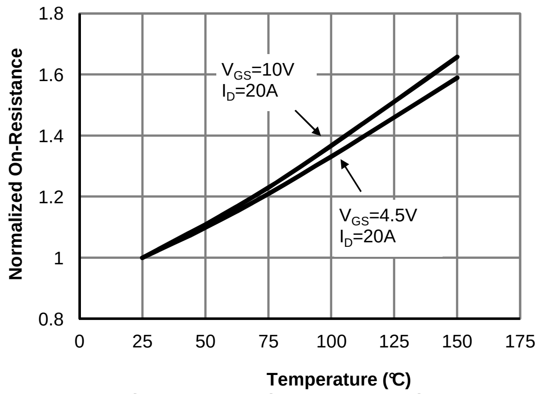


Figure 4: On-Resistance vs. Junction Temperature (Note E)

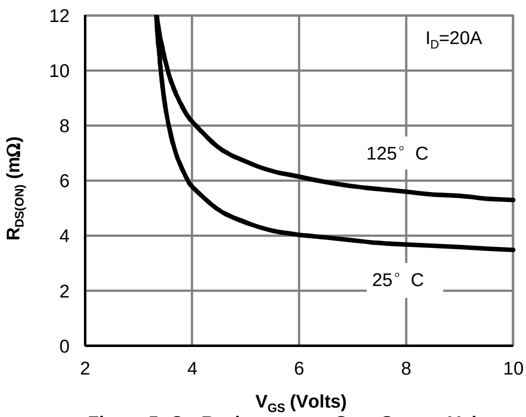


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

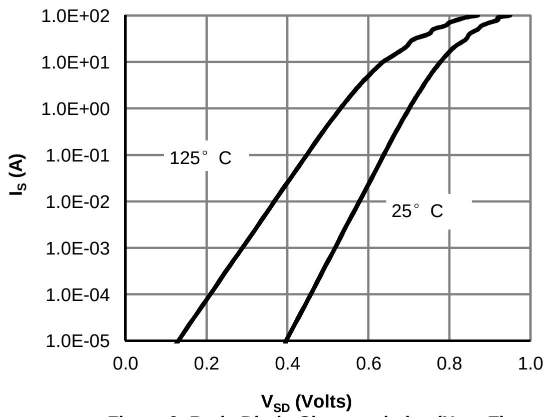


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

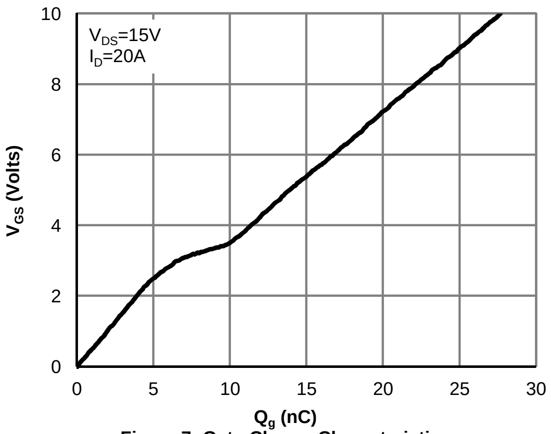


Figure 7: Gate-Charge Characteristics

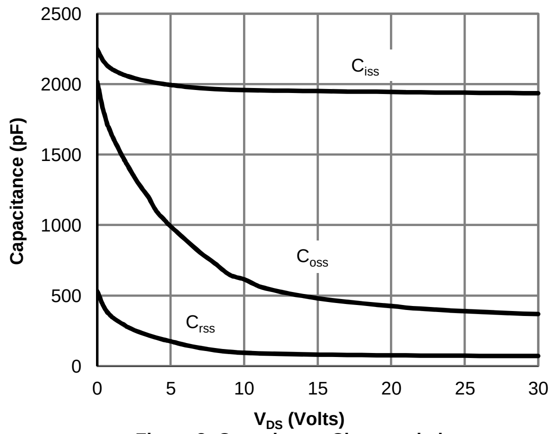
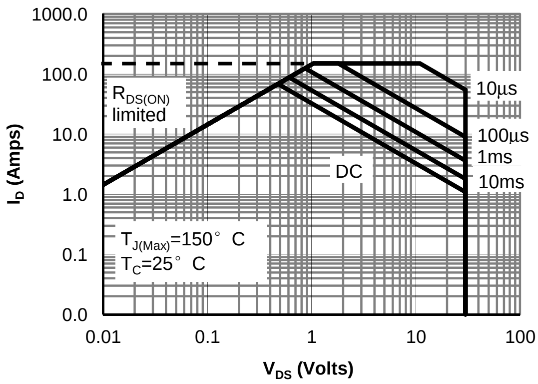
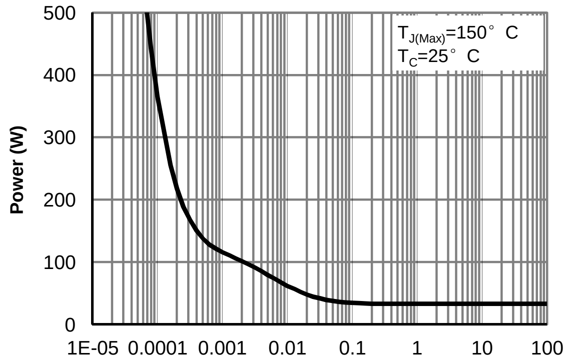


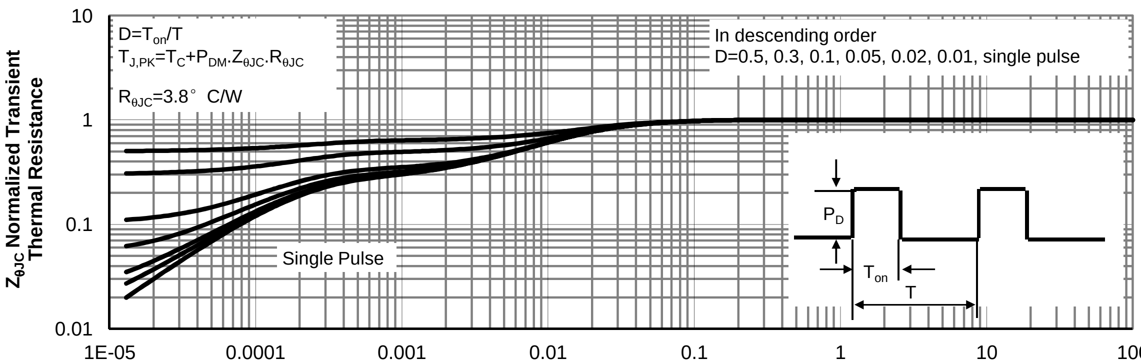
Figure 8: Capacitance Characteristics



V_{GS}> or equal to 4.5V
Figure 9: Maximum Forward Biased Safe Operating Area (Note F)



Pulse Width (s)
Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)



Pulse Width (s)
Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

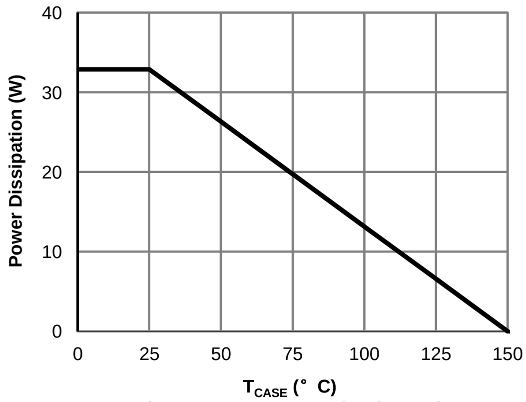


Figure 12: Power De-rating (Note F)

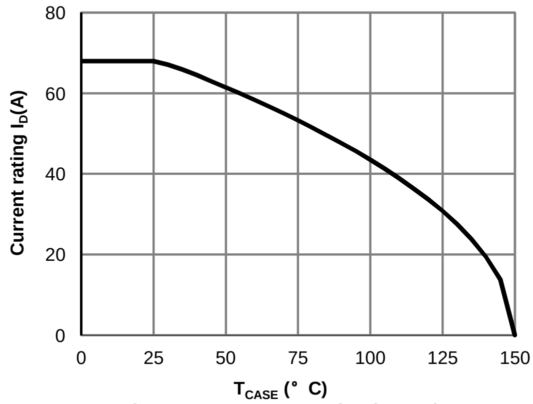


Figure 13: Current De-rating (Note F)

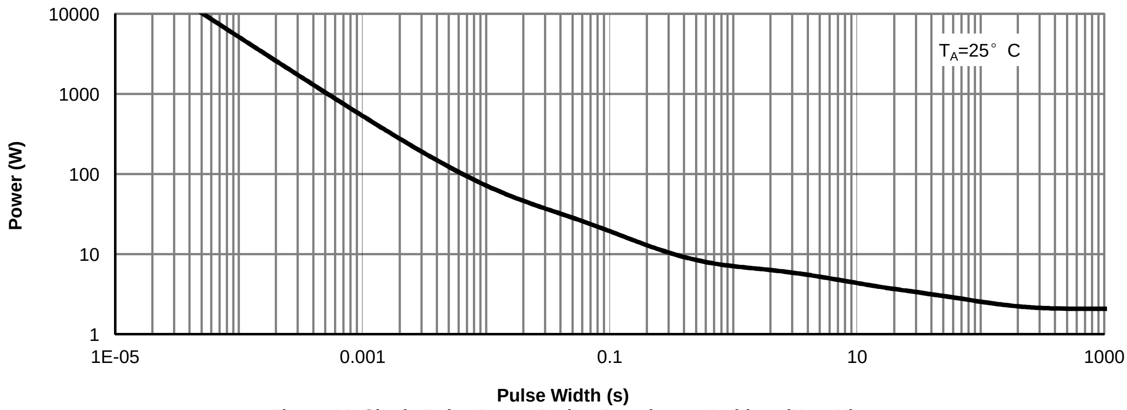


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

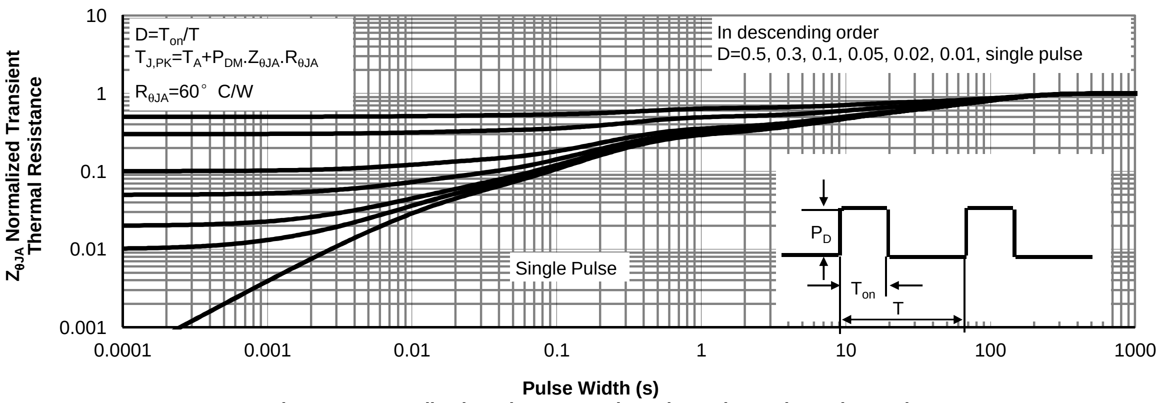
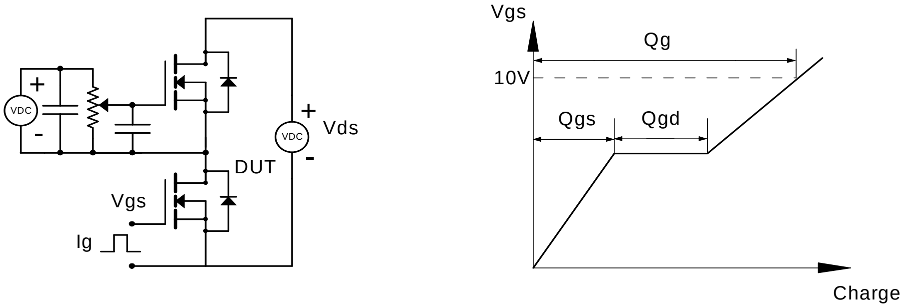
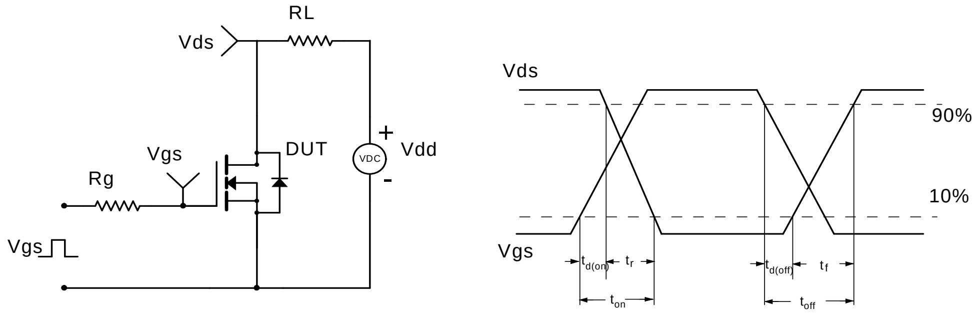


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

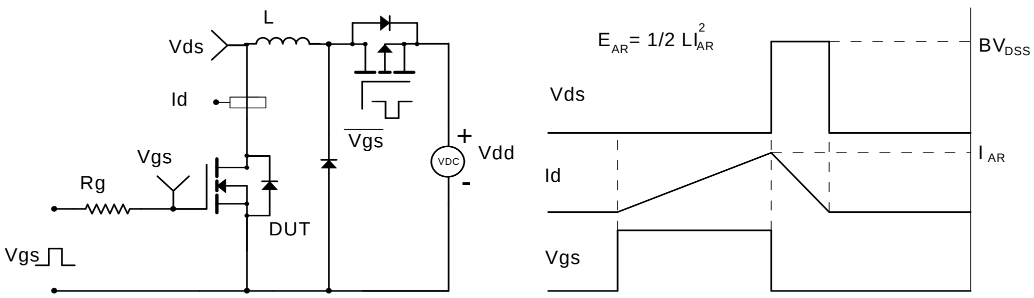
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms